Ordering number : EN8636

SANYO Semiconductors
DATA SHEET

An ON Semiconductor Company

N-Channel Junction Silicon FET

2SK3796 — Low-Frequency General-Purpose Amplifier, Impedance Converter Applications

Applicatins

- Low-frequency general-purpose amplifier, impedance conversion, analog switches applications.

Features

- Small I_{GSS}.
- Small Ciss

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSX}		30	V
Gate-to-Drain Voltage	V_{GDS}		–30	V
Gate Current	I_G		10	mA
Drain Current	I_D		10	mA
Allowable Power Dissipation	P_D		100	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Drain Breakdown Voltage	$V_{(BR)GDS}$	I_G=–10μA, V_{DS}=0V	–30			V
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=–20V, V_{DS}=0V			–1.0	nA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1μA	–0.18	–0.95	–2.2	V

Marking : K

Continued on next page.

SANYO Semiconductor Co., Ltd.
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain Current	I_{DSS}	V_{DS}=10V, V_{GS}=0V	0.6*		6.0*	mA
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, V_{GS}=0V, f=1kHz	3.0	6.5		mS
Input Capacitance	Ciss	V_{DS}=10V, V_{GS}=0V, f=1MHz		4		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, V_{GS}=0V, f=1MHz		1.1		pF
Static Drain-to-Source On-State Resistance	R_{DS}(on)	V_{DS}=10mV, V_{GS}=0V		200		Ω

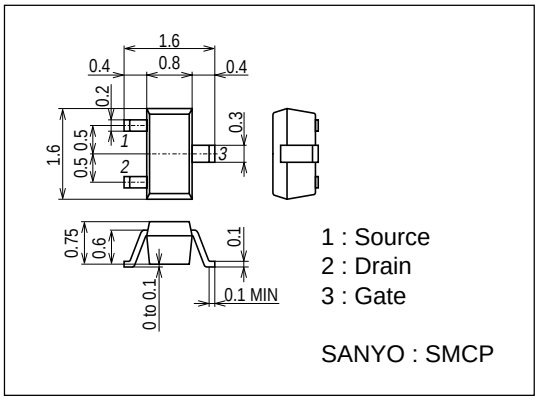
* : The 2SK3796 is classified by I_{DSS} as follows : (unit : mA).

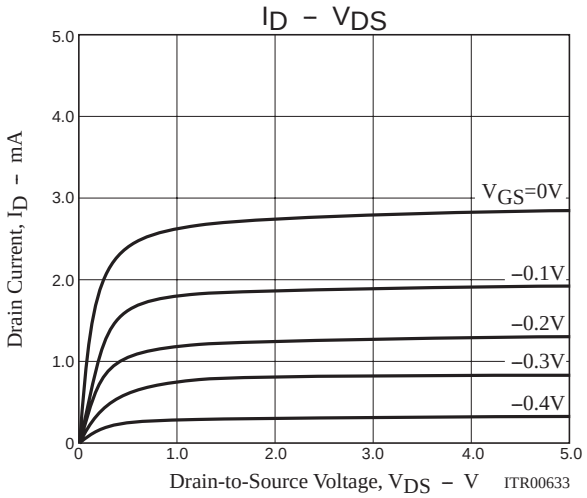
Rank	2	3	4
I_{DSS}	0.6 to 1.5	1.2 to 3.0	2.5 to 6.0

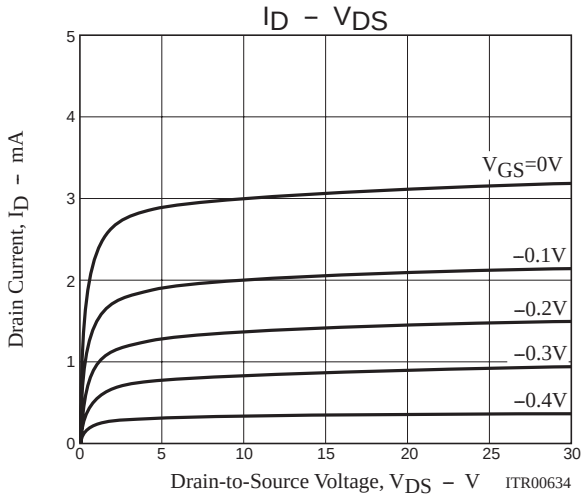
Package Dimensions

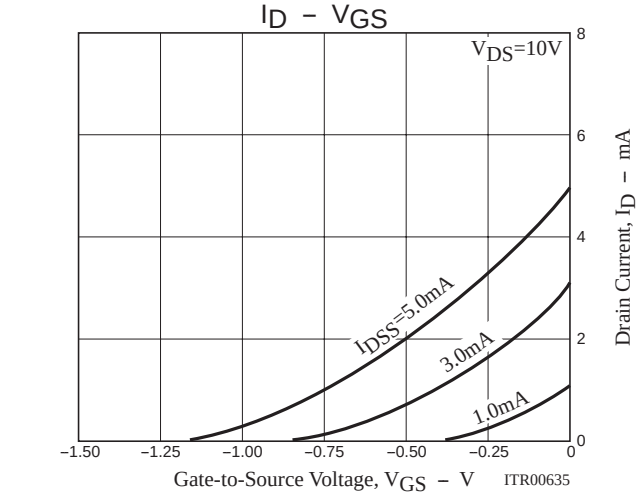
unit : mm (unit)

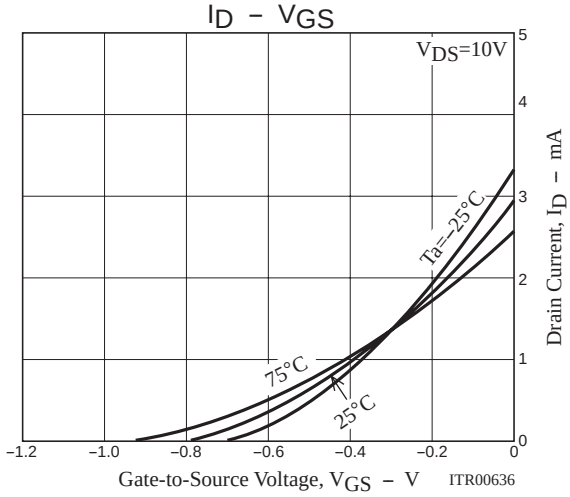
7027-003

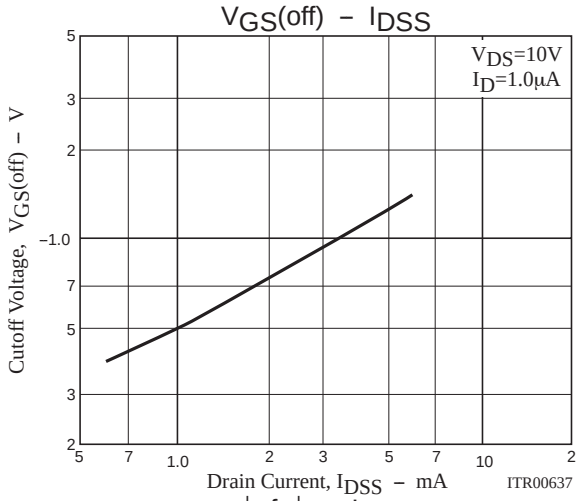


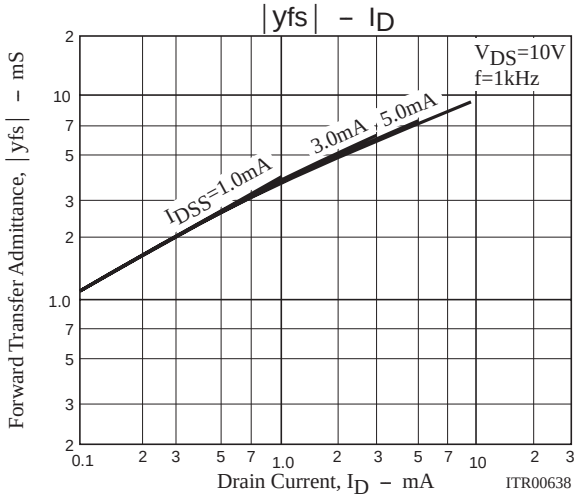


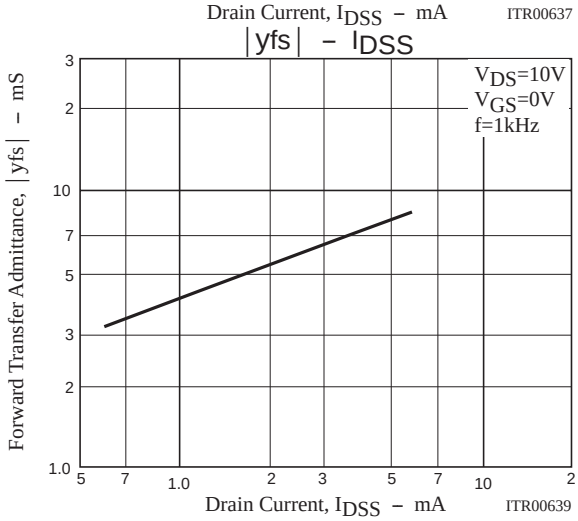


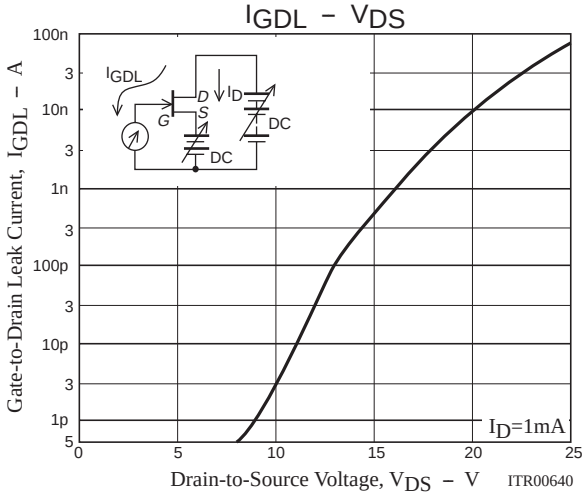


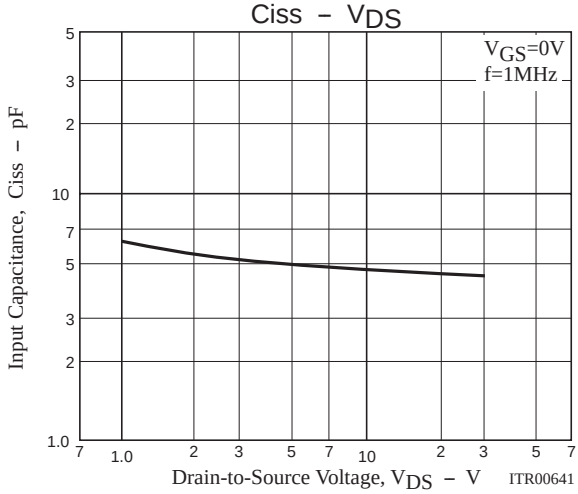


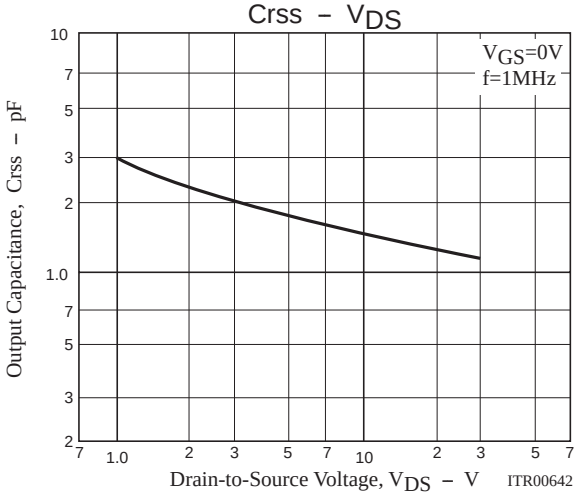

VGS(off) – IDSS
VDS=10V
ID=1.0μA
Cutoff Voltage, VGS(off) – V
Drain Current, IDSS – mA
ITR00637

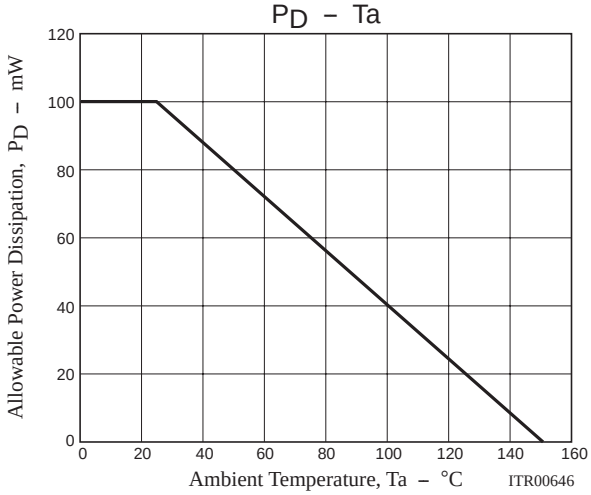

|yfs| – ID
VDS=10V
f=1kHz
IDSS=1.0mA
3.0mA
5.0mA
Forward Transfer Admittance, |yfs| – mS
Drain Current, ID – mA
ITR00638


|yfs| – IDSS
VDS=10V
VGS=0V
f=1kHz
Forward Transfer Admittance, |yfs| – mS
Drain Current, IDSS – mA
ITR00639


IGDL – VDS
IGDL
D
ID
G
S
DC
DC
ID=1mA
Gate-to-Drain Leak Current, IGDL – A
Drain-to-Source Voltage, VDS – V
ITR00640


Ciss – VDS
VGS=0V
f=1MHz
Input Capacitance, Ciss – pF
Drain-to-Source Voltage, VDS – V
ITR00641


Crss – VDS
VGS=0V
f=1MHz
Output Capacitance, Crss – pF
Drain-to-Source Voltage, VDS – V
ITR00642


PD – Ta
Allowable Power Dissipation, PD – mW
Ambient Temperature, Ta – °C
ITR00646